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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
HITOSHI KATO, ET AL. : EXAMINER: TO BE ASSIGNED
SERIAL NO: 10/518,025 :
FILED: DECEMBER 15, 2004 : GROUP ART UNIT: TO BE ASSIGNED
FOR: CVD METHOD FOR FORMING :
SILICON NITRIDE FILM ON TARGET
SUBSTRATE

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Remarks/Arguments begin on page 3 of this paper.